

HUTSON INDUSTRIES

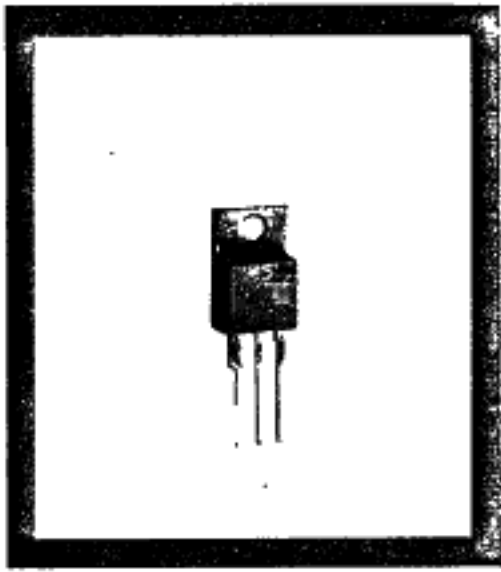
TRIAC's



ISOTAB* TRIACS
ELECTRICALLY ISOLATED

TO-220

8 AMPERE
10 AMPERE
15 AMPERE

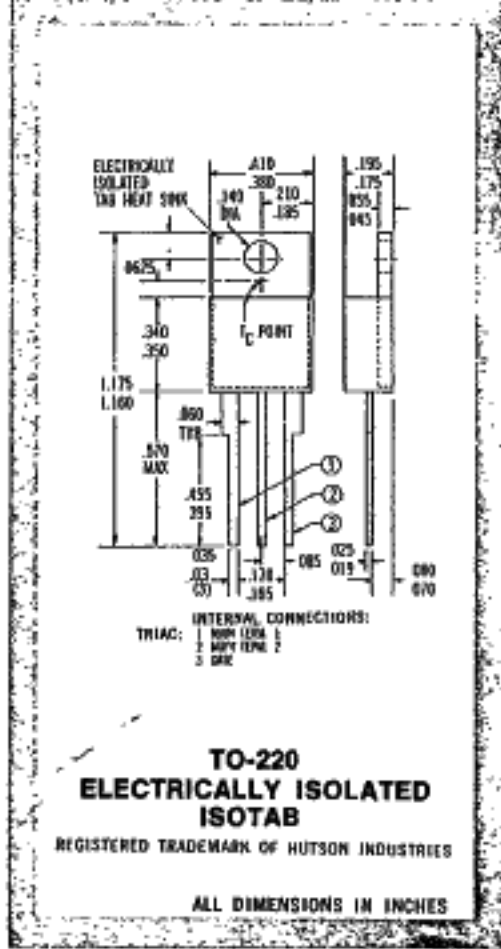


Hutson ISOTAB*-packaged triacs featuring an improved electrical isolation technique, will withstand a minimum of 1600 VAC from leads to tab for one minute at 80°C case temperature. Hermetically sealed within this package is a dense, void-free-glass passivated, hermetically-sealed chip. ISOTAB triacs have a low thermal impedance and are available in wide range of current and voltage ratings, from 8 to 15 Amperes and 50 to 600 Volts. The 15 Amp versions feature Beryllium Oxide isolation for further improved thermal characteristics.

These economical, highly reliable triacs are the result of Hutson's advanced engineering and manufacturing technology, and experience in switching-device applications.

These Hutson triacs are bi-directional triode thyristors and may be switched from off-state to conduction for either polarity of applied voltage with positive or negative gate triggering. They are designed for control of AC loads in applications such as lighting, heating, and motor speed controls, and static switching relays.

In addition to these plastic packaged triacs, Hutson offers other package configurations in current ratings to 60 Amperes and Voltage (V_{DRM}) ratings to 1000V. All Hutson triacs are available in chip form. For additional information, please consult Hutson Industries.



* Trademark of Hutson Industries.

HUTSON INDUSTRIES

P. O. BOX 34235 • 2019 W. VALLEY VIEW LANE
DALLAS, TEXAS 75234 (214) 241-3511
TWX 910-860-5537



ISOT 00008-12

		SYMBOL	V_{DROM}	DEVICE NOS. (NOTE 1)			UNITS
MAXIMUM RATINGS	Repetitive Peak Off-State Voltage, Gate Open, and $T_J = 100^\circ\text{C}$	V_{DROM}	50 100 200 300 400 500 600	08 18 28 38 48 58 68	010 110 210 310 410 510 610	015 115 215 315 415 515 615	VOLT
	RMS On-State Current at $T_C = 75^\circ\text{C}$ and Conduction Angle of 180°	I_{IRMS}		8	10	15	AMP
	Peak Surge (Non-Repetitive) On-State Current, One-Cycle, at 50Hz or 60Hz	I_{TSM}		100	100	150	AMP
	Peak Gate-Trigger Current for $3\mu\text{sec}$, Max.	I_{GTM}		3	4	4	AMP
	Peak Gate-Power Dissipation at $I_{GT} \leq I_{GTM}$ for $3\mu\text{sec}$, Max.	P_{GM}		20	40	40	WATT
	Average Gate-Power Dissipation	$P_{G(AV)}$		0.2	0.5	0.8	WATT
	Storage Temperature Range	T_{stg}		← -40 to +150 →			$^\circ\text{C}$
	Operating Temperature Range, T_C	$T_{oper.}$		← -40 to +100 →			$^\circ\text{C}$
ELECTRICAL CHARACTERISTICS At Maximum Ratings and at Specific Case Temperatures	Peak Off-State Current, Gate Open, $T_J = 100^\circ\text{C}$ $V_{DROM} = \text{Max. Rating}$	I_{DROM}		2.0 MAX	2.0 MAX	2.0 MAX	mA
	Maximum On-State Voltage at $T_C = 25^\circ\text{C}$ (Peak)	V_F		2.2 MAX	2.2 MAX	2.2 MAX	VOLTS
	Peak On-State Current			11	14	21	AMP
	DC Holding Current, Gate Open and $T_C = 25^\circ\text{C}$	I_{HO}		50 MAX	50 MAX	50 MAX	mA
	Critical Rate-of-Rise of Off-State Voltage for $V_D = V_{DROM}$, Gate Open, $T_C = 100^\circ\text{C}$	Critical dv/dt		5 TYP	5 TYP	5 TYP	V/ μsec
	DC Gate-Trigger Current for $V_D = 12\text{VDC}$, $R_L = 30\Omega$ and at $T_C = 25^\circ\text{C}$ ($T_2 + \text{Gate} +$, $T_2 - \text{Gate} -$) Quads I and III ($T_2 + \text{Gate} -$, $T_2 - \text{Gate} +$) Quads II and IV (Note 2)	I_{GT}		50 MAX 80 MAX	50 MAX 80 MAX	50 MAX 80 MAX	mA mA
	DC Gate-Trigger Voltage for $V_D = 12\text{VDC}$, $R_L = 30\Omega$ and at $T_C = 25^\circ\text{C}$	V_{GT}		2.5 MAX	2.5 MAX	2.5 MAX	VOLTS
	Gate-Controlled Turn-on Time for $V_D = V_{DROM}$, $I_{GT} = 80\text{mA}$, $t_r = 0.1\mu\text{sec}$, $I_T = 10\text{A}$ (Peak) and $T_C = 25^\circ\text{C}$	t_{GT}		2.5 TYP	2.5 TYP	2.5 TYP	μSEC
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		2.5 TYP	2.5 TYP	*1.5 TYP	$^\circ\text{C/W}$	

ALL VALUES APPLY IN EITHER DIRECTION

*BeO Substrate

IS ϕ TT 00008-2X

ISOTAB (ELECTRICALLY ISOLATED) TRIACS

DEVICE NO. DESIGNATION

NOTE 1: I = ELECTRICALLY ISOLATED

T = TRIAC

0 to 6 = 50 to 600 V (V_{BO}) RATING
 8, 10, 15 = 8A, 10A & 15A ($I_{T(RMS)}$)

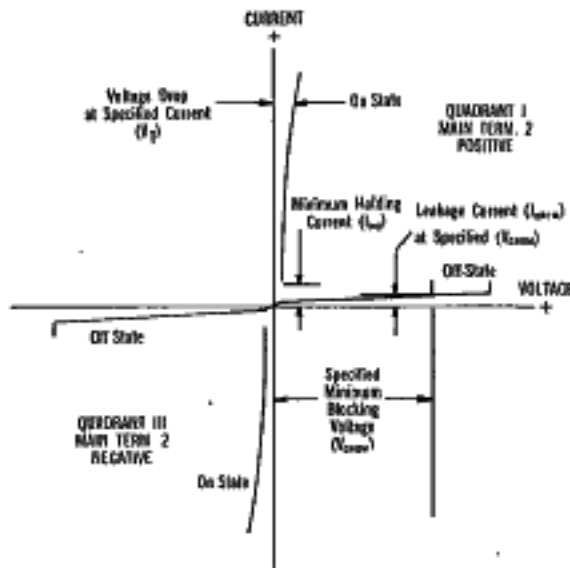
NOTE 2: I_{or} CHARACTERISTICS:

NO SUFFIX = 50 mA, I & III QUADS;
 80 mA, II & IV QUADS;
 A = 50 mA I & III QUADS ONLY
 B = 100 mA I & III QUADS ONLY
 HA = 25 mA I & III QUADS ONLY
 HX = 25 mA I & III QUADS 40 mA, QUADS II & IV

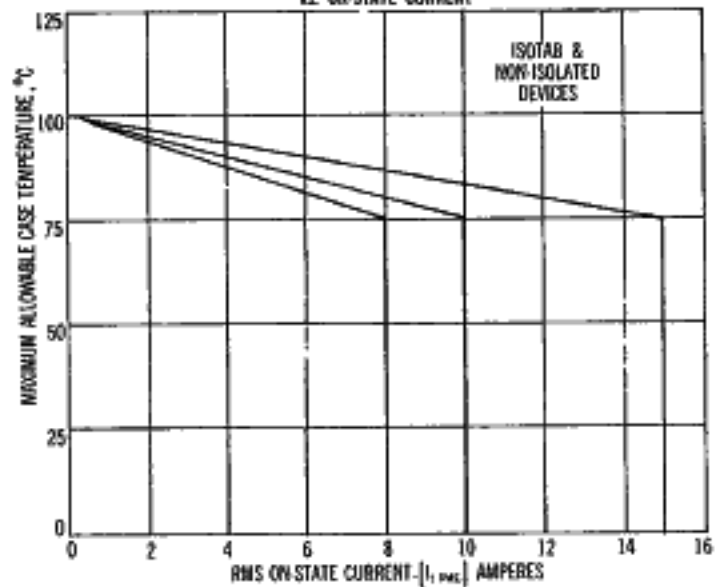
EXAMPLE
 I T 4 8 A

Example Device No.
 would be:
 an Electrically
 isolated Triac,
 400 V (V_{BO}),
 8A ($I_{T(RMS)}$) with
 50 mA (I_{or})
 Quads I & III

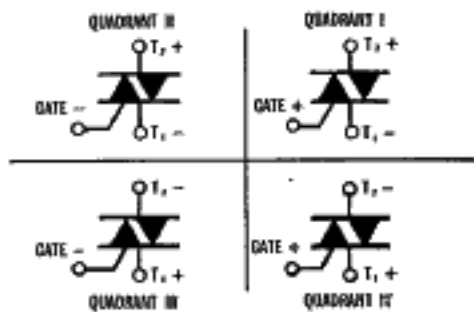
TYPICAL VOLTAGE-CURRENT CHARACTERISTICS



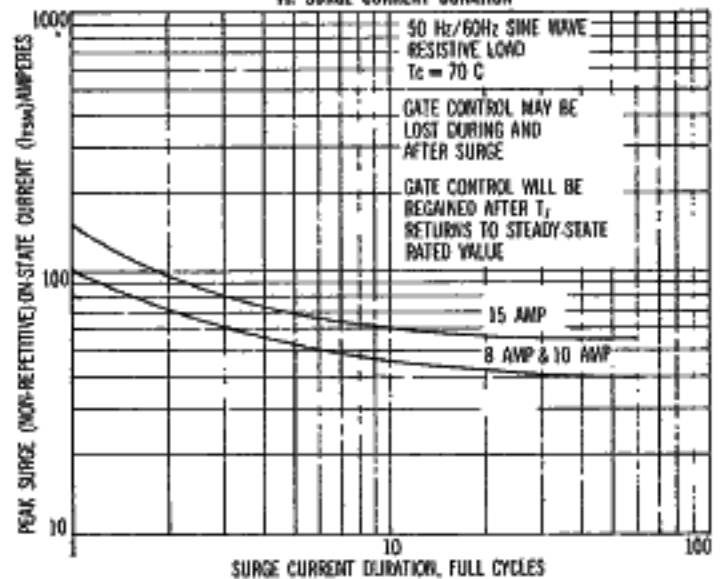
MAXIMUM ALLOWABLE CASE TEMPERATURE vs. ON-STATE CURRENT



DEFINITION OF QUADRANTS



PEAK SURGE ON-STATE CURRENT vs. SURGE CURRENT DURATION



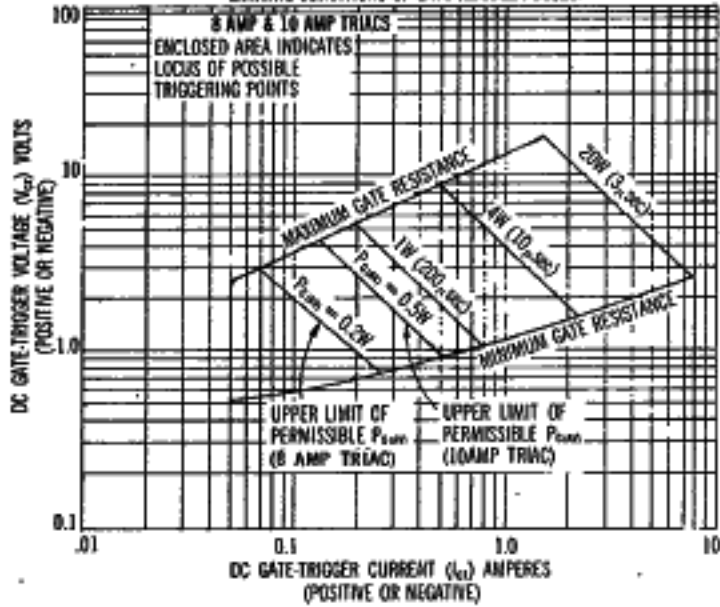
HUTSON INDUSTRIES
 BOX 34235 • 2019 W. VALLEY VIEW LANE
 DALLAS, TEXAS 75234 (214) 241-3511
 TWX 910-860-5537

ISPTT-00008-3X

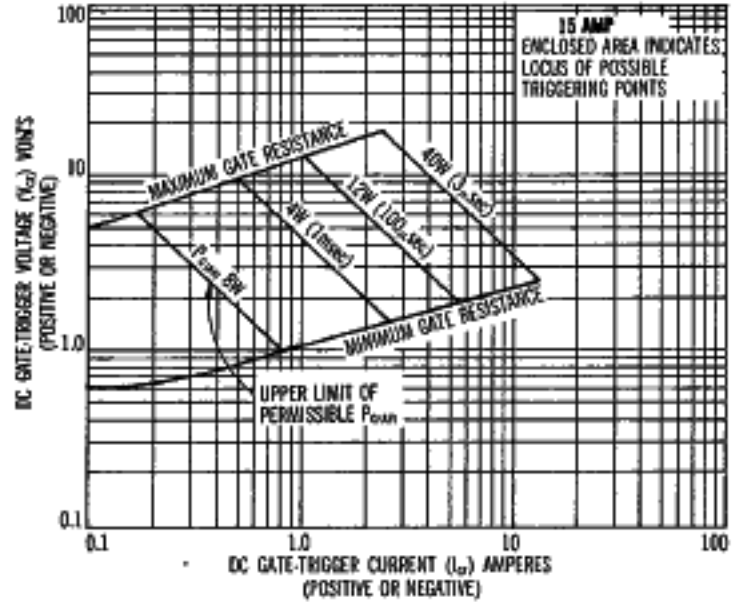
HUTSON INDUSTRIES 8A, 10A, 15A ISOTAB (ELECTRICALLY ISOLATED) TRIACS

www.DataSheet4U.com

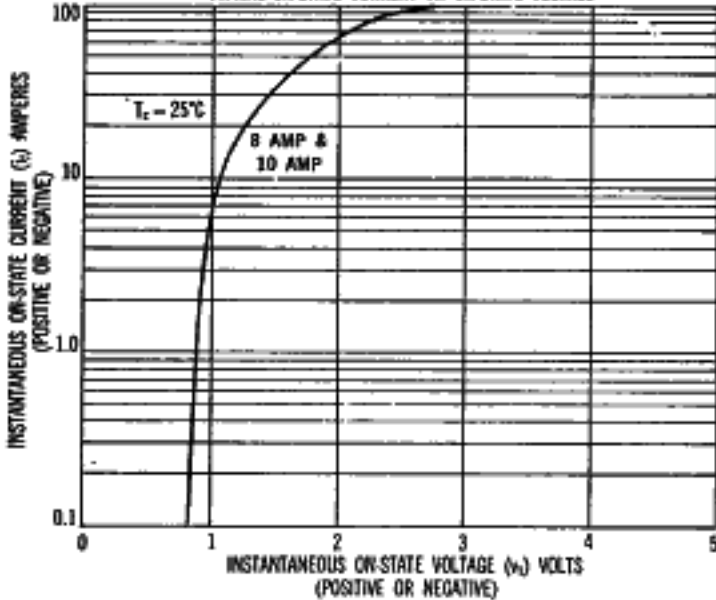
GATE-TRIGGER CHARACTERISTICS AND
LIMITING CONDITIONS OF GATE-TRIGGER PULSES.



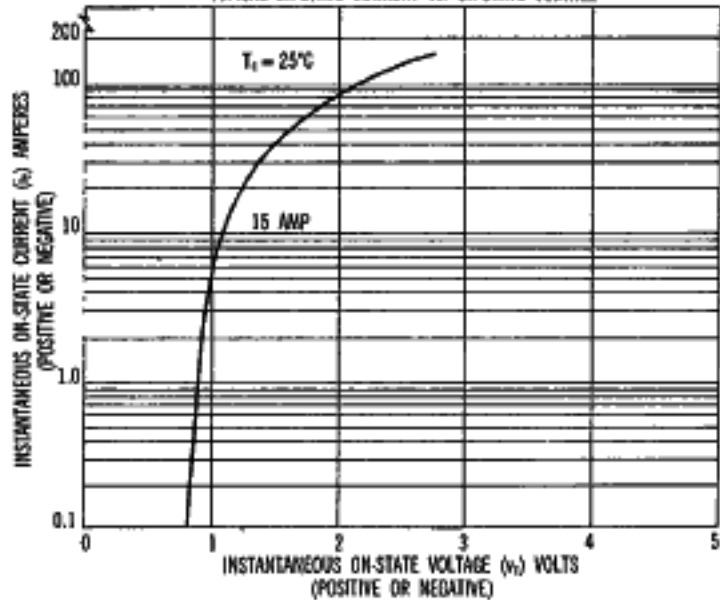
GATE-TRIGGER CHARACTERISTICS AND
LIMITING CONDITIONS OF GATE-TRIGGER PULSES.



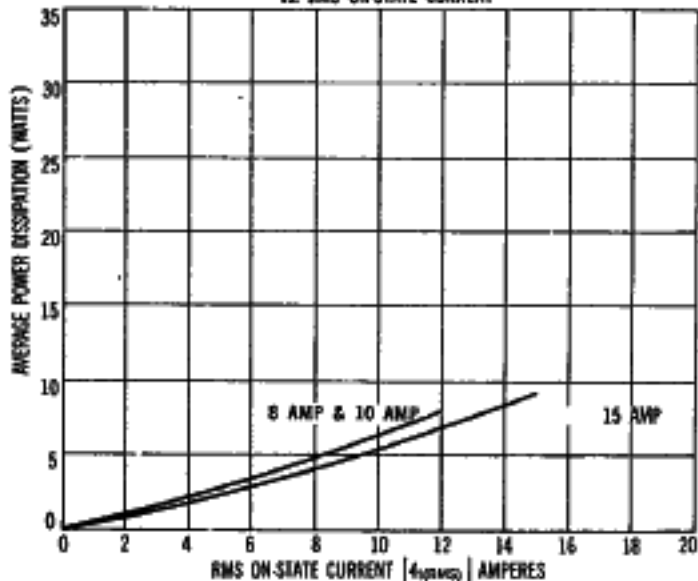
TYPICAL ON-STATE CURRENT vs. ON-STATE VOLTAGE



TYPICAL ON-STATE CURRENT vs. ON-STATE VOLTAGE



TYPICAL AVERAGE POWER DISSIPATION
vs. RMS ON-STATE CURRENT



HUTSON INDUSTRIES

2018 W. VALLEY VIEW LANE
DALLAS, TEXAS 75234 (214) 241-3511
TWX 910-860-5537

EUROPEAN OFFICE:
30 RUE PIERRE SEMARD,
YERRES, 91, FRANCE
TEL: Paris 825-8258
TELEX 21311

ISOTT00008-4X

Hutson Industries, Inc. reserves the right to make changes in specifications at any time and without notice to improve design and/or performance of their products.

The information furnished by Hutson in this publication is believed to be accurate and reliable. However, no responsibility is assumed by Hutson for its use; nor for any infringements of patents or other rights of third parties resulting from its use. No license either expressed or implied is granted under any www.DataSheet4U.com rights of Hutson Industries, Inc.